

SIPMOS[®] Small-Signal-Transistor

Feature

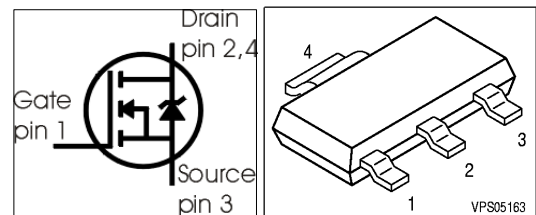
- N-Channel
- Enhancement mode
- Logic Level
- dv/dt rated
- Pb-free lead plating; RoHS compliant
- Qualified according to AEC Q101



Product Summary

| | | |
|--------------|------|----------|
| V_{DS} | 100 | V |
| $R_{DS(on)}$ | 6 | Ω |
| I_D | 0.37 | A |

PG-SOT223



| Type | Package | Tape and Reel Information | Marking | Packaging |
|--------|-----------|---------------------------|---------|-----------|
| BSP123 | PG-SOT223 | L6433: 4000 pcs/reel | BSP123 | Non dry |
| BSP123 | PG-SOT223 | L6327: 1000 pcs/reel | BSP123 | Non dry |

Maximum Ratings, at $T_j = 25^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Value | Unit |
|--|----------------------|--------------------------|-------------------|
| Continuous drain current $T_A=25^\circ\text{C}$ $T_A=70^\circ\text{C}$ | I_D | 0.37 0.3 | A |
| Pulsed drain current $T_A=25^\circ\text{C}$ | $I_{D \text{ puls}}$ | 1.48 | |
| Reverse diode dv/dt $I_S=0.37\text{A}$, $V_{DS}=80\text{V}$, $di/dt=200\text{A}/\mu\text{s}$, $T_{jmax}=150^\circ\text{C}$ | dv/dt | 6 | kV/ μs |
| Gate source voltage | V_{GS} | ± 20 | V |
| ESD Class JESD22-A114-HBM | | 0 (<250V) | |
| Power dissipation $T_A=25^\circ\text{C}$ | P_{tot} | 1.79 | W |
| Operating and storage temperature IEC climatic category; DIN IEC 68-1 | T_j , T_{stg} | -55... +150 55/150/56 | $^\circ\text{C}$ |

Thermal Characteristics

| Parameter | Symbol | Values | | | Unit |
|---|------------|--------|------|------|------|
| | | min. | typ. | max. | |
| Characteristics | | | | | |
| Thermal resistance, junction - soldering point (Pin 4) | R_{thJS} | - | 15 | 25 | K/W |
| SMD version, device on PCB: | R_{thJA} | | | | |
| @ min. footprint | | - | 100 | 115 | |
| @ 6 cm ² cooling area ¹⁾ | | - | 51 | 70 | |

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|--|---------------|--------|------|-----------|---------------|
| | | min. | typ. | max. | |
| Static Characteristics | | | | | |
| Drain-source breakdown voltage $V_{GS}=0, I_D=250\mu\text{A}$ | $V_{(BR)DSS}$ | 100 | - | - | V |
| Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D=50\mu\text{A}$ | $V_{GS(th)}$ | 0.8 | 1.4 | 1.8 | |
| Zero gate voltage drain current $V_{DS}=100\text{V}, V_{GS}=0, T_j=25^\circ\text{C}$ $V_{DS}=100\text{V}, V_{GS}=0, T_j=150^\circ\text{C}$ | I_{DSS} | - | - | 0.01 5 | μA |
| Gate-source leakage current $V_{GS}=20\text{V}, V_{DS}=0$ | I_{GSS} | - | - | 10 | |
| Drain-source on-state resistance $V_{GS}=2.8\text{V}, I_D=15\text{mA}$ | $R_{DS(on)}$ | - | 14 | 30 | Ω |
| Drain-source on-state resistance $V_{GS}=4.5\text{V}, I_D=0.3\text{A}$ | $R_{DS(on)}$ | - | 4.8 | 10 | |
| Drain-source on-state resistance $V_{GS}=10\text{V}, I_D=0.37\text{A}$ | $R_{DS(on)}$ | - | 3.5 | 6 | |

¹⁾Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (single layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Values | | | Unit |
|-----------|--------|------------|--------|------|------|------|
| | | | min. | typ. | max. | |

Dynamic Characteristics

| | | | | | | |
|------------------------------|--------------|---|------|------|------|----|
| Transconductance | g_{fs} | $V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 0.3\text{A}$ | 0.13 | 0.27 | - | S |
| Input capacitance | C_{iss} | $V_{GS} = 0$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$ | - | 56 | 70 | pF |
| Output capacitance | C_{oss} | | - | 9 | 11.3 | |
| Reverse transfer capacitance | C_{rss} | | - | 3.5 | 4.4 | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD} = 50\text{V}$, $V_{GS} = 10\text{V}$, $I_D = 0.37\text{A}$, $R_G = 6\Omega$ | - | 3.3 | 5 | ns |
| Rise time | t_r | | - | 3.2 | 4.8 | |
| Turn-off delay time | $t_{d(off)}$ | | - | 8.7 | 13 | |
| Fall time | t_f | | - | 9.4 | 14 | |

Gate Charge Characteristics

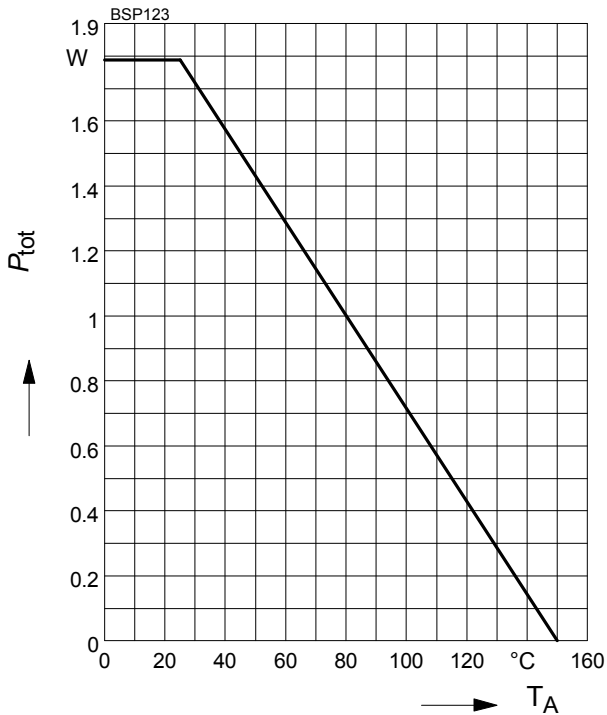
| | | | | | | |
|-----------------------|-----------------|--|---|------|------|----|
| Gate to source charge | Q_{gs} | $V_{DD} = 80\text{V}$, $I_D = 0.37\text{A}$ | - | 0.09 | 0.13 | nC |
| Gate to drain charge | Q_{gd} | | - | 0.8 | 1.2 | |
| Gate charge total | Q_g | $V_{DD} = 80\text{V}$, $I_D = 0.37\text{A}$, $V_{GS} = 0$ to 10V | - | 1.6 | 2.4 | |
| Gate plateau voltage | $V_{(plateau)}$ | $V_{DD} = 80\text{V}$, $I_D = 0.37\text{A}$ | - | 3.61 | - | V |

Reverse Diode

| | | | | | | |
|--|----------|---|---|------|------|----|
| Inverse diode continuous forward current | I_S | $T_A = 25\text{ }^\circ\text{C}$ | - | - | 0.37 | A |
| Inv. diode direct current, pulsed | I_{SM} | | - | - | 1.48 | |
| Inverse diode forward voltage | V_{SD} | $V_{GS} = 0$, $I_F = I_S$ | - | 0.9 | 1.2 | V |
| Reverse recovery time | t_{rr} | $V_R = 50\text{V}$, $I_F = I_S$, $di_F/dt = 100\text{A}/\mu\text{s}$ | - | 52.7 | 79 | ns |
| Reverse recovery charge | Q_{rr} | | - | 17.8 | 27 | |

1 Power dissipation

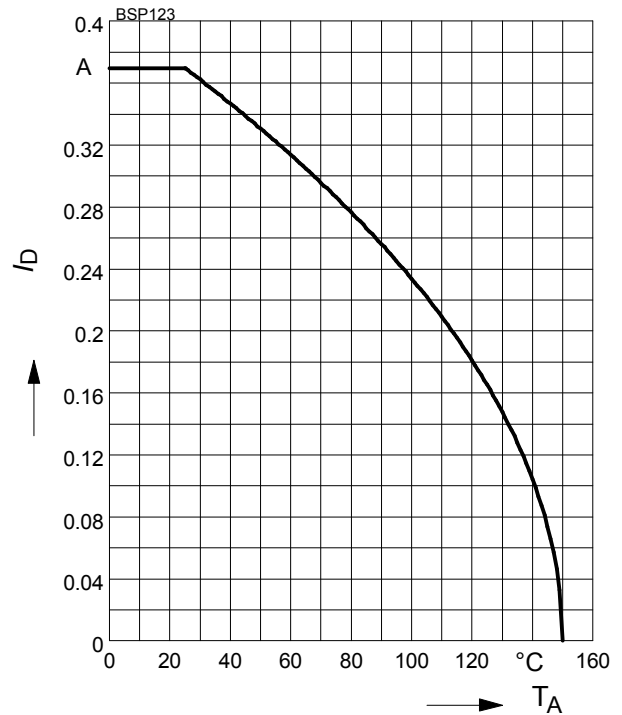
$$P_{tot} = f(T_A)$$



2 Drain current

$$I_D = f(T_A)$$

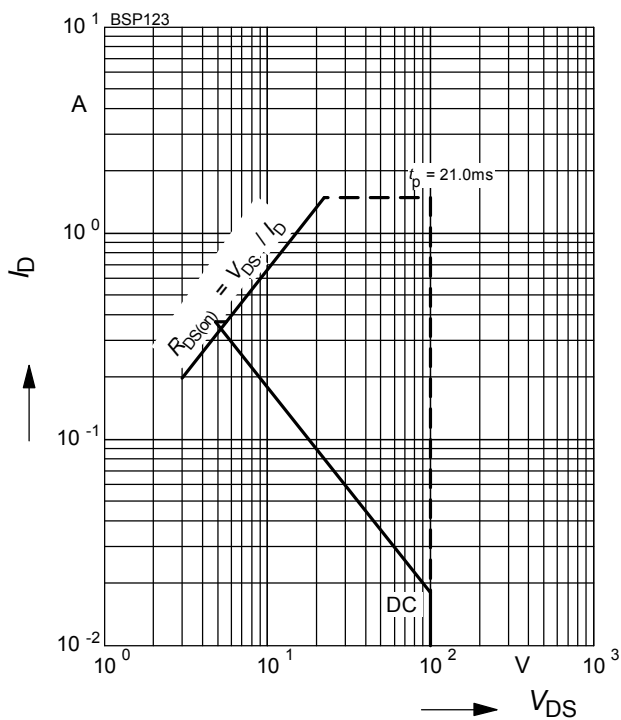
parameter: $V_{GS} \geq 10\text{ V}$



3 Safe operating area

$$I_D = f(V_{DS})$$

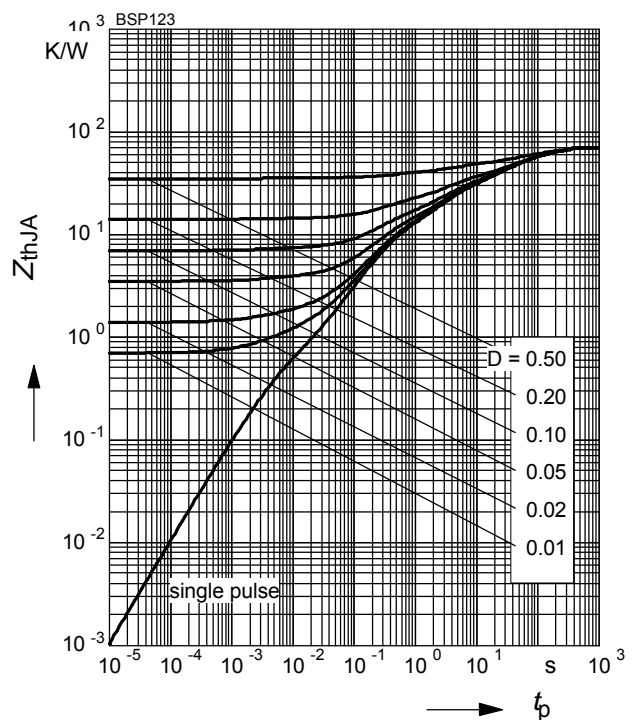
parameter: $D = 0, T_A = 25\text{ °C}$



4 Transient thermal impedance

$$Z_{thJA} = f(t_p)$$

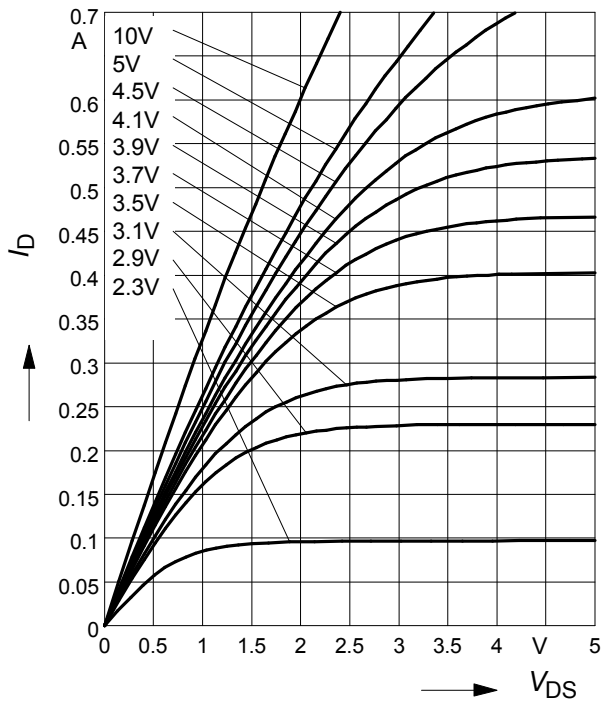
parameter: $D = t_p/T$



5 Typ. output characteristic

$$I_D = f(V_{DS})$$

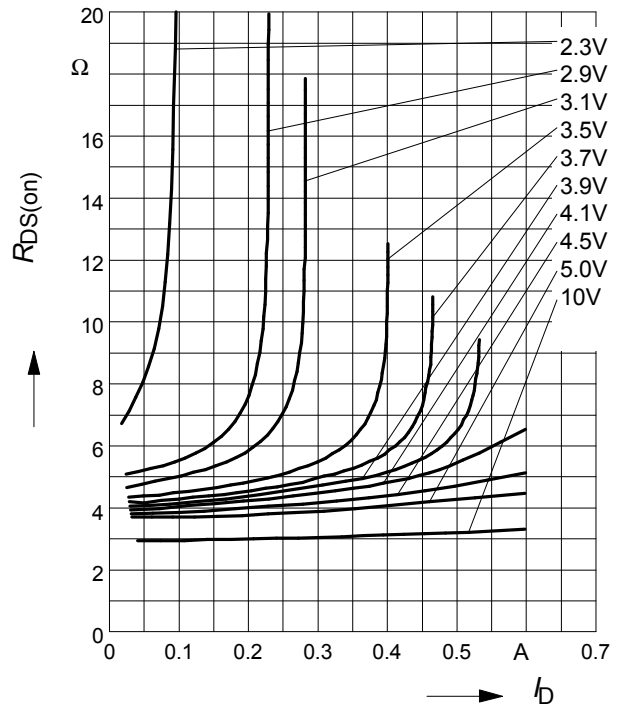
parameter: $T_j = 25\text{ }^\circ\text{C}$, V_{GS}



6 Typ. drain-source on resistance

$$R_{DS(on)} = f(I_D)$$

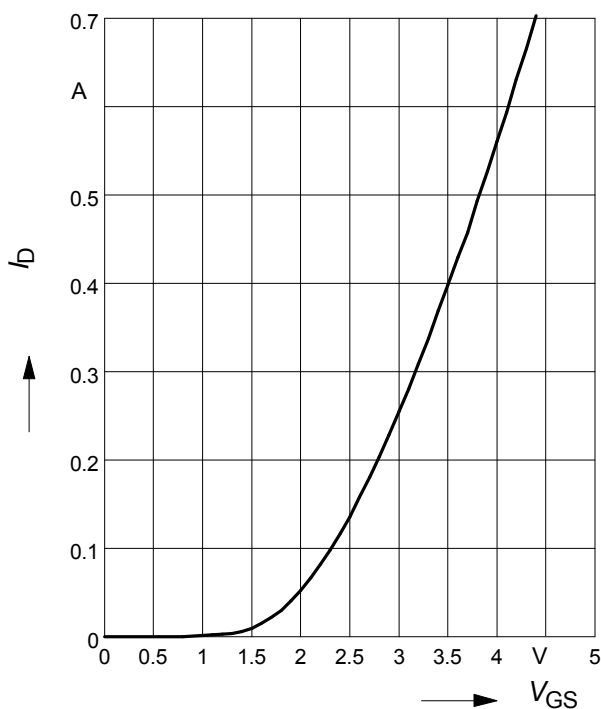
parameter: $T_j = 25\text{ }^\circ\text{C}$, V_{GS}



7 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

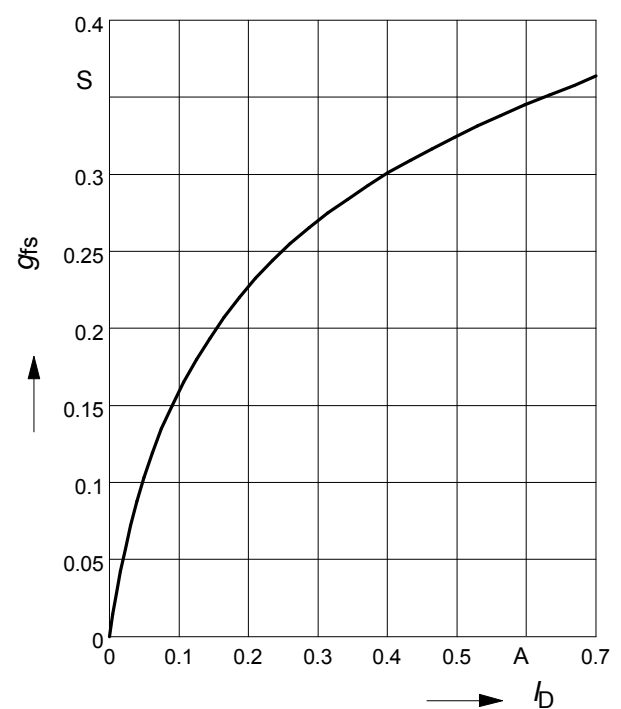
parameter: $T_j = 25\text{ }^\circ\text{C}$



8 Typ. forward transconductance

$$g_{fs} = f(I_D)$$

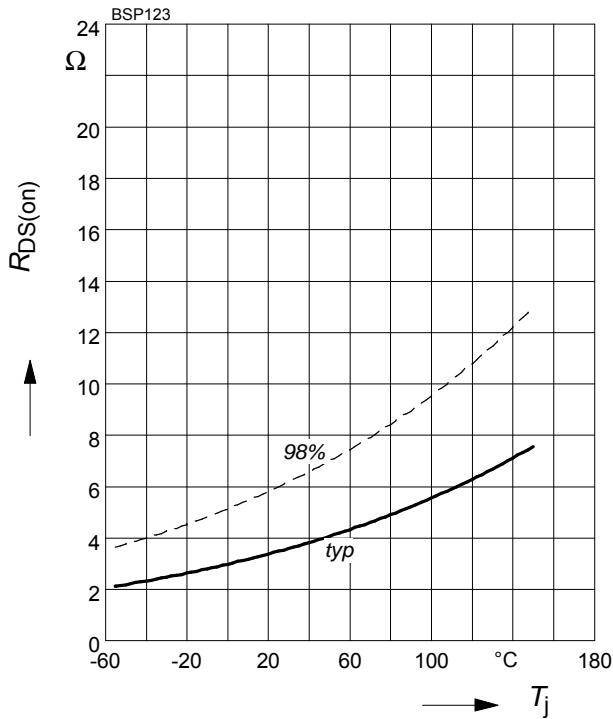
parameter: $T_j = 25\text{ }^\circ\text{C}$



9 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

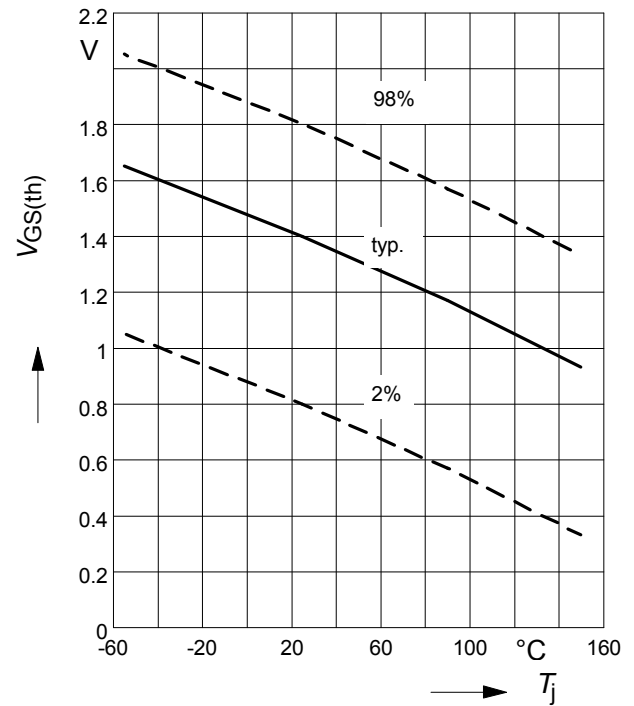
parameter: $I_D = 0.37\text{ A}$, $V_{GS} = 10\text{ V}$



10 Typ. gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

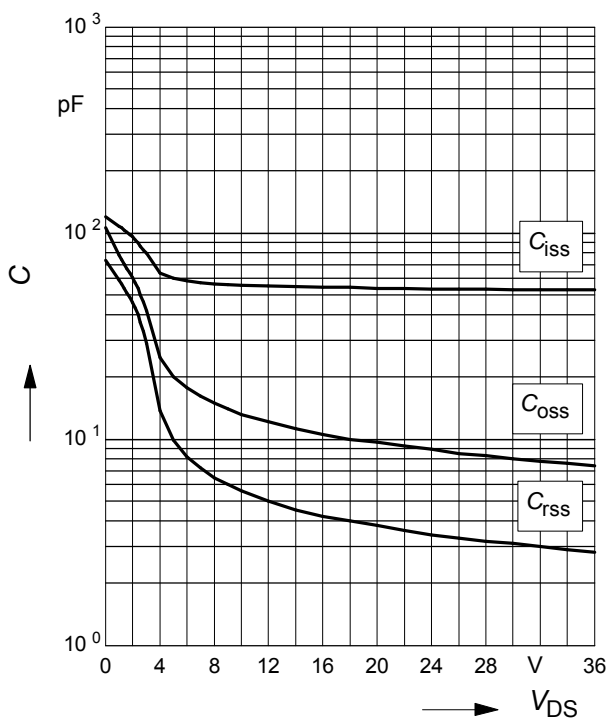
parameter: $V_{GS} = V_{DS}$; $I_D = 50\mu\text{A}$



11 Typ. capacitances

$$C = f(V_{DS})$$

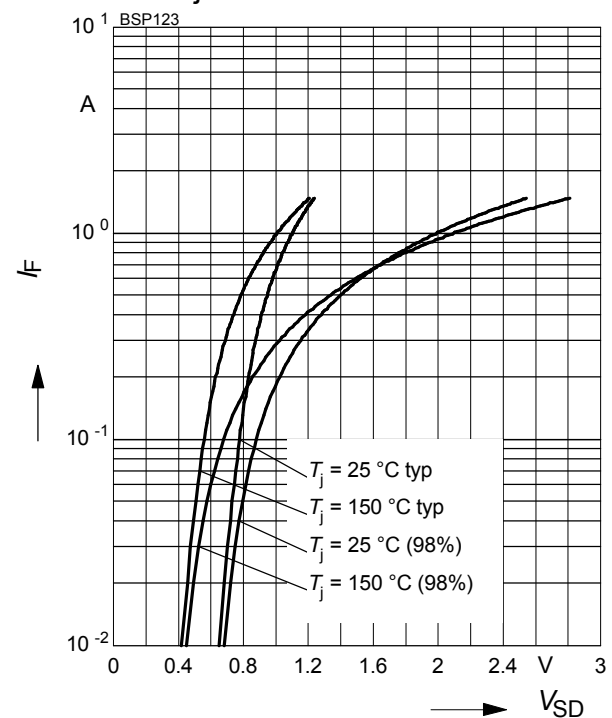
parameter: $V_{GS} = 0$, $f = 1\text{ MHz}$, $T_j = 25\text{ }^\circ\text{C}$



12 Forward character. of reverse diode

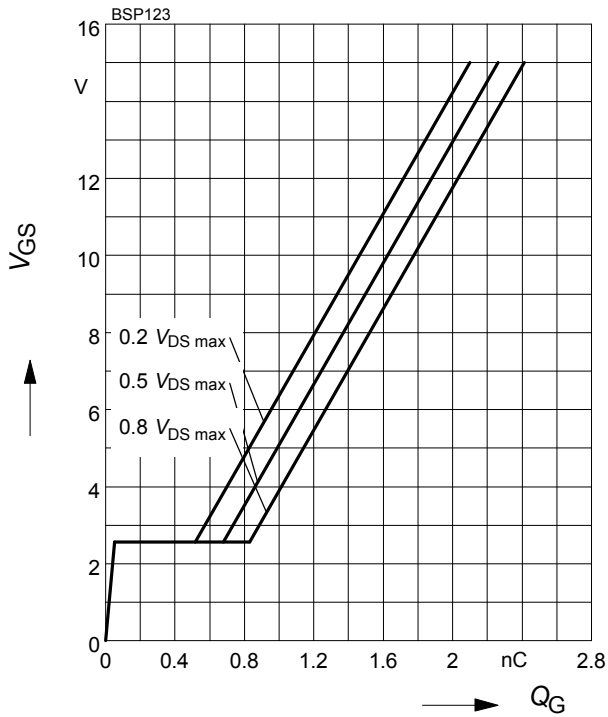
$$I_F = f(V_{SD})$$

parameter: T_j



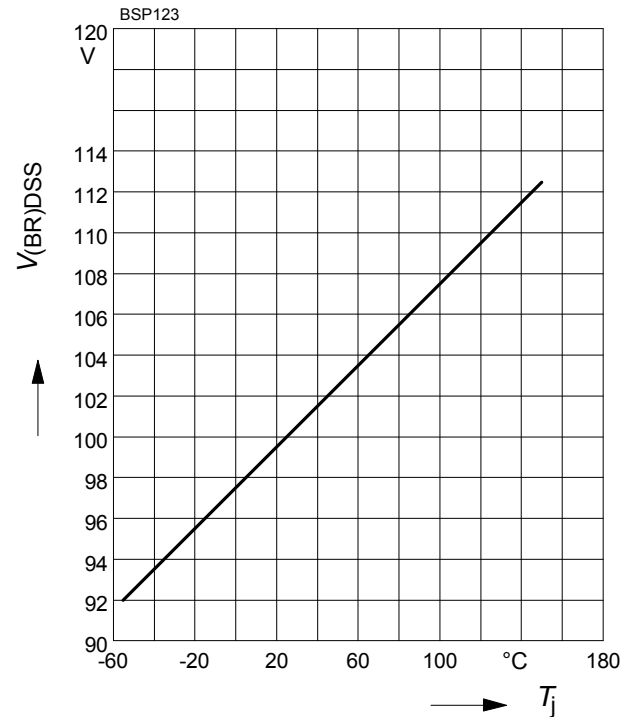
13 Typ. gate charge

$V_{GS} = f(Q_G)$; parameter: V_{DS} ,
 $I_D = 0.37\text{ A pulsed}$, $T_j = 25\text{ °C}$



14 Drain-source breakdown voltage

$V_{(BR)DSS} = f(T_j)$



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